

| Ref # | Hits    | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|---------|--|---|------------------|---------|------------------|
| L1    | 2984580 | memory or storage  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 17:55 |
| L2    | 7844    | 1 and cell with source with float\$5   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:04 |
| L3    | 8716    | 1 and cell with (source or drain) with float\$5  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:05 |
| L4    | 63      | 1 and cell with second adj transistor with (source or drain) with float\$5             | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:11 |
| L5    | 493     | 3 not floating adj gate  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:11 |
| L6    | 186     | 5 and cell with transistor with (source or drain) with float\$5                        | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:11 |
| L7    | 18      | 5 and cell with (second or first) adj3 transistor with (source or drain) with float\$5 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:30 |
| L8    | 6       | 5 and cell with transistor with series with (source or drain) with float\$5            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:33 |
| L9    | 369150  | 1 and cell not floating adj gate   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:35 |
| L10   | 166     | 9 and cell with transistor with source with float\$5                                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:36 |
| L11   | 10      | 10 and second adj transistor with cell   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:43 |
| L12   | 3877    | reduc\$5 with leak\$5 with cell  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2004/12/19 18:44 |

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| L13 | 9     | 11 and (writ\$5 or program\$5) with cell                             | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:46 |
| L14 | 1379  | 12 and (writ\$5 or program\$5) with cell                             | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:46 |
| L15 | 5     | 14 and ground with gate with first adj transistor with cell          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:48 |
| L16 | 5     | 15 and (voltage or potential) with source with first adj2 transistor | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:55 |
| L17 | 51443 | writ\$5 with cell  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:56 |
| L18 | 45    | 17 and ground with gate with first adj transistor with cell          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:57 |
| L19 | 9     | 18 and reference with source with first adj transistor               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:59 |
| L20 | 9     | 19 and second adj transistor   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 18:59 |
| L21 | 6     | 19 and second adj transistor with cell                               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 19:01 |
| L22 | 5     | 21 and leak\$5   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR | ON | 2004/12/19 19:02 |